

## Excellent Integrated System Limited

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

[Vishay/Siliconix](#)

[SI7655DN-T1-GE3](#)

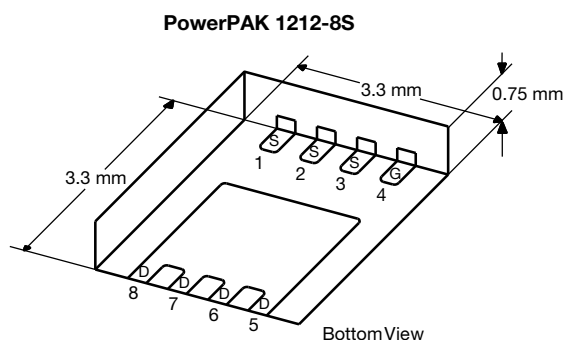
For any questions, you can email us directly:

[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)



## P-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)
- 20	0.0036 at V <sub>GS</sub> = - 10 V	- 40 <sup>e</sup>	72 nC
	0.0048 at V <sub>GS</sub> = - 4.5 V	- 40 <sup>e</sup>	
	0.0085 at V <sub>GS</sub> = - 2.5 V	- 40 <sup>e</sup>	



**Ordering Information:**  
Si7655DN-T1-GE3 (Lead (Pb)-free and Halogen-free)

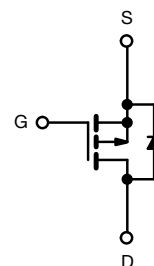
### FEATURES

- TrenchFET® Power MOSFET
- Low Thermal Resistance PowerPAK® Package with Small Size and Low 0.75 mm Profile
- 100 % R<sub>g</sub> and UIS Tested
- Material categorization: For definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### APPLICATIONS

- Smart Phones, Tablet PCs, Mobile Computing
  - Battery Switch
  - Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C, unless otherwise noted)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	- 20	V
Gate-Source Voltage		V <sub>GS</sub>	± 12	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C	I <sub>D</sub>	- 40 <sup>e</sup>	A
	T <sub>C</sub> = 70 °C		- 40 <sup>e</sup>	
	T <sub>A</sub> = 25 °C		- 31 <sup>a, b</sup>	
	T <sub>A</sub> = 70 °C		- 25 <sup>a, b</sup>	
Pulsed Drain Current (t = 300 μs)		I <sub>DM</sub>	- 100	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C	I <sub>S</sub>	- 40 <sup>e</sup>	
	T <sub>A</sub> = 25 °C		- 4 <sup>a, b</sup>	
Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 20	mJ
Single-Pulse Avalanche Energy		E <sub>AS</sub>	20	
Maximum Power Dissipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	57	W
	T <sub>C</sub> = 70 °C		36	
	T <sub>A</sub> = 25 °C		4.8 <sup>a, b</sup>	
	T <sub>A</sub> = 70 °C		3 <sup>a, b</sup>	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 50 to 150	°C
Soldering Recommendations (Peak Temperature) <sup>c, d</sup>			260	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. t = 10 s.

c. See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAK 1212-8S is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

e. Package limited.

# Si7655DN

Vishay Siliconix



## THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a, b</sup>	$t \leq 10$ s	$R_{thJA}$	21	26	°C/W
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	1.7	2.2	

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Maximum under steady state conditions is 63 °C/W.

## SPECIFICATIONS ( $T_J = 25$ °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA	- 20			V	
V <sub>DS</sub> Temperature Coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	I <sub>D</sub> = - 250 μA		- 12		mV/ °C	
V <sub>GS(th)</sub> Temperature Coefficient	ΔV <sub>GS(th)</sub> /T <sub>J</sub>			2.6			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 0.5		- 1.1	V	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = ± 12 V			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V			- 1	μA	
		V <sub>DS</sub> = - 20 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C			- 10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≤ - 5 V, V <sub>GS</sub> = - 10 V	- 20			A	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		0.0030	0.0036	Ω	
		V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 15 A		0.0039	0.0048		
		V <sub>GS</sub> = - 2.5 V, I <sub>D</sub> = - 10 A		0.0062	0.0085		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 20 A		90		S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz		6600		pF	
Output Capacitance	C <sub>oss</sub>			890			
Reverse Transfer Capacitance	C <sub>rss</sub>			930			
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 20 A		150	225	nC	
		V <sub>DS</sub> = - 10 V, V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 20 A		72	110		
					12		
					19		
Gate-Source Charge	Q <sub>gs</sub>						
Gate-Drain Charge	Q <sub>gd</sub>						
Gate Resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.6	5.2	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 1 Ω I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 4.5 V, R <sub>g</sub> = 1 Ω		45	90	ns	
Rise Time	t <sub>r</sub>			45	90		
Turn-Off DelayTime	t <sub>d(off)</sub>			100	200		
Fall Time	t <sub>f</sub>			35	70		
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> = - 10 V, R <sub>L</sub> = 1 Ω I <sub>D</sub> ≅ - 10 A, V <sub>GEN</sub> = - 10 V, R <sub>g</sub> = 1 Ω		13	25		
Rise Time	t <sub>r</sub>			10	20		
Turn-Off DelayTime	t <sub>d(off)</sub>			110	220		
Fall Time	t <sub>f</sub>			25	50		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C			- 40 <sup>c</sup>	A	
Pulse Diode Forward Current <sup>a</sup>	I <sub>SM</sub>				- 100		
Body Diode Voltage	V <sub>SD</sub>	I <sub>F</sub> = - 10 A		- 0.75	- 1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = - 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		30	60	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>			17	26	nC	
Reverse Recovery Fall Time	t <sub>a</sub>			15		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			15			

Notes:

a. Pulse test; pulse width  $\leq 300$   $\mu$ s, duty cycle  $\leq 2$  %.

b. Guaranteed by design, not subject to production testing.

c. Package limited.

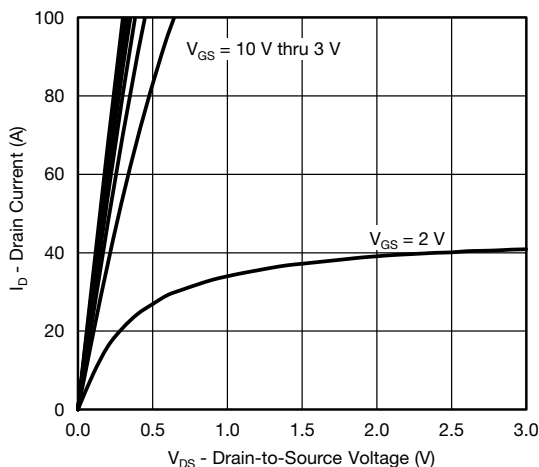
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



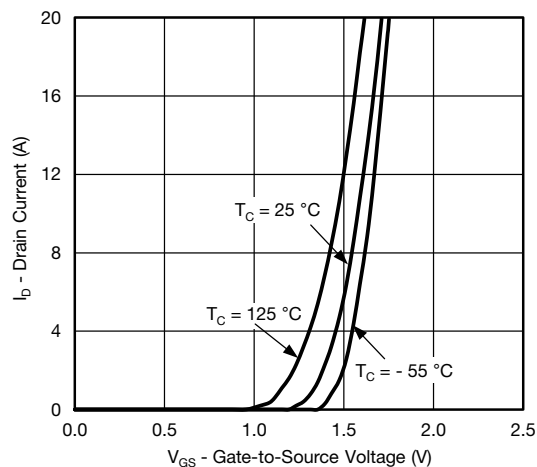
**Si7655DN**

Vishay Siliconix

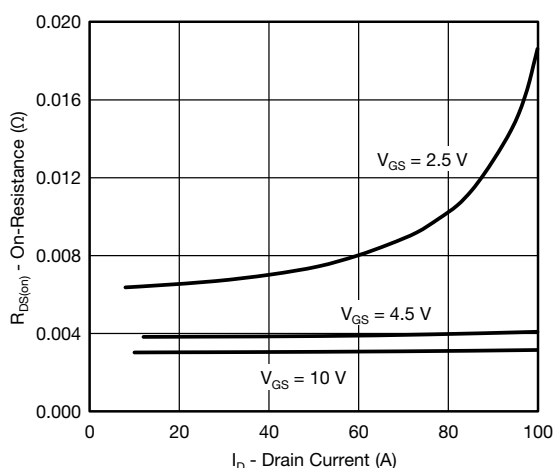
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



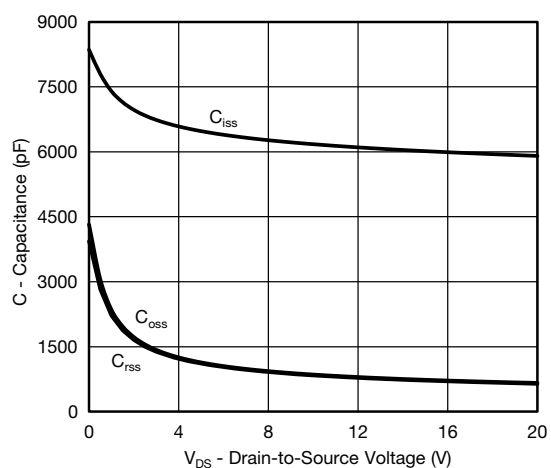
**Output Characteristics**



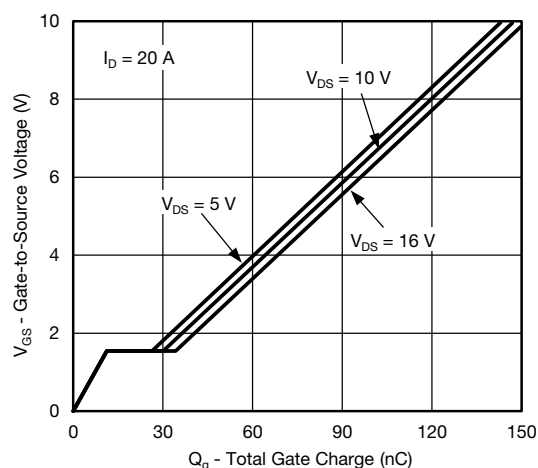
**Transfer Characteristics**



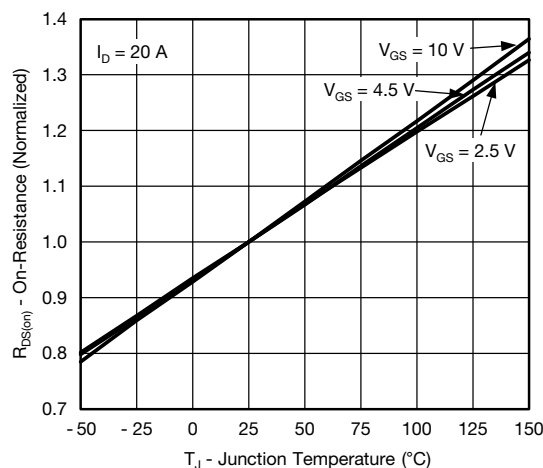
**On-Resistance vs. Drain Current and Gate Voltage**



**Capacitance**



**Gate Charge**



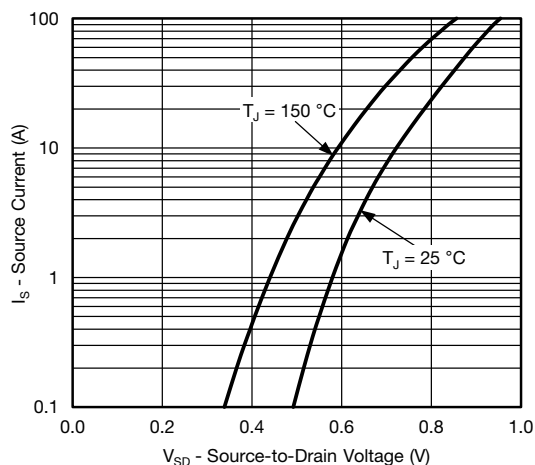
**On-Resistance vs. Junction Temperature**

# Si7655DN

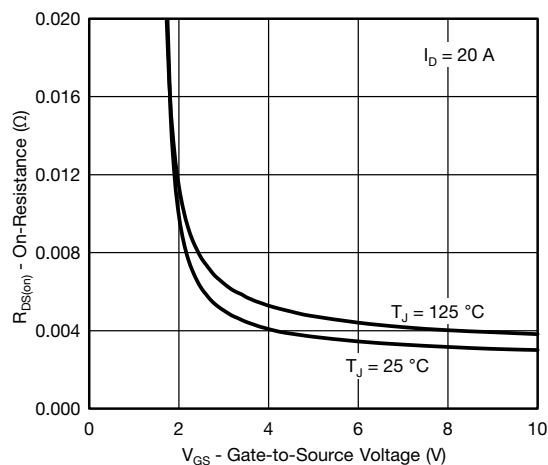
Vishay Siliconix



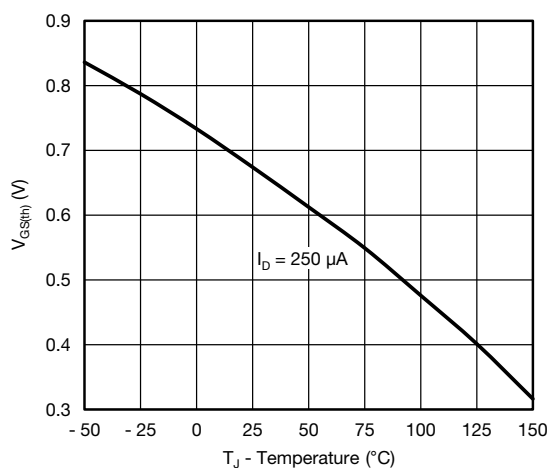
## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



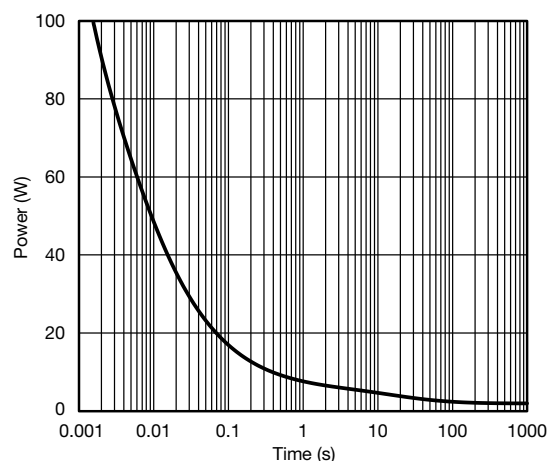
Source-Drain Diode Forward Voltage



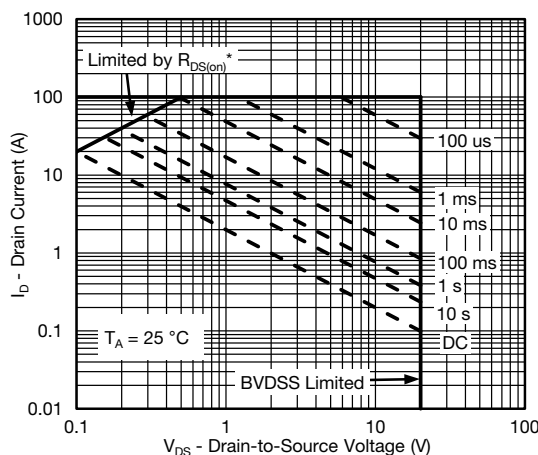
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



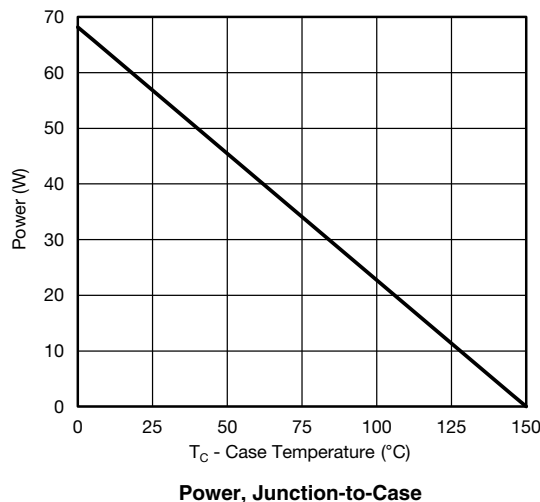
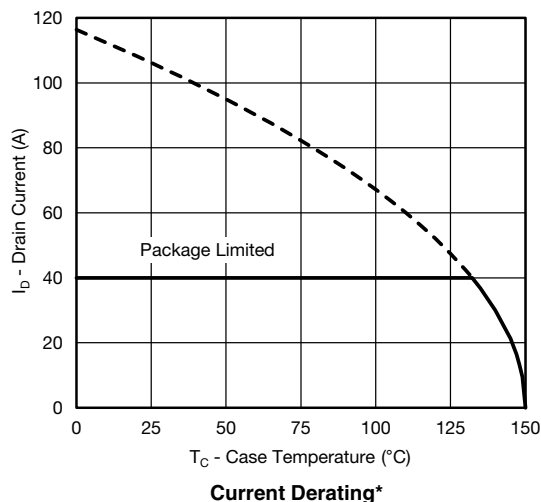
Single Pulse Power, Junction-to-Ambient



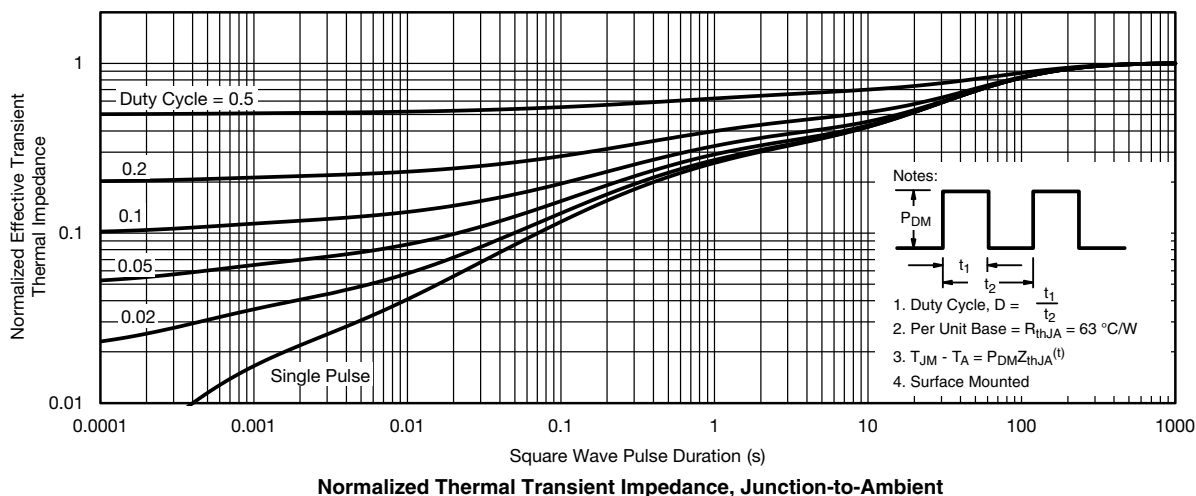
Safe Operating Area, Junction-to-Ambient



**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

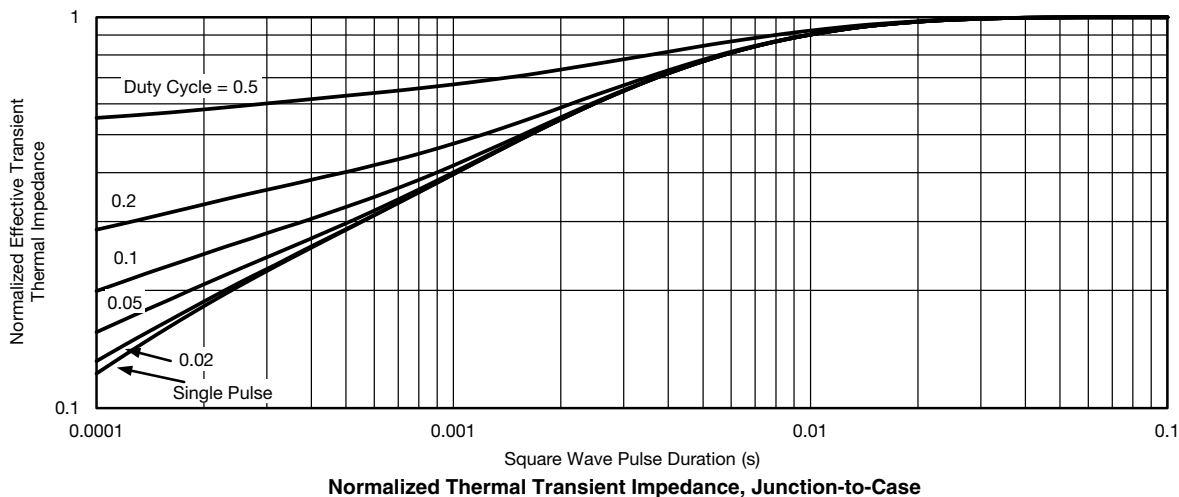


## Si7655DN

Vishay Siliconix



### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg263617](http://www.vishay.com/ppg263617).

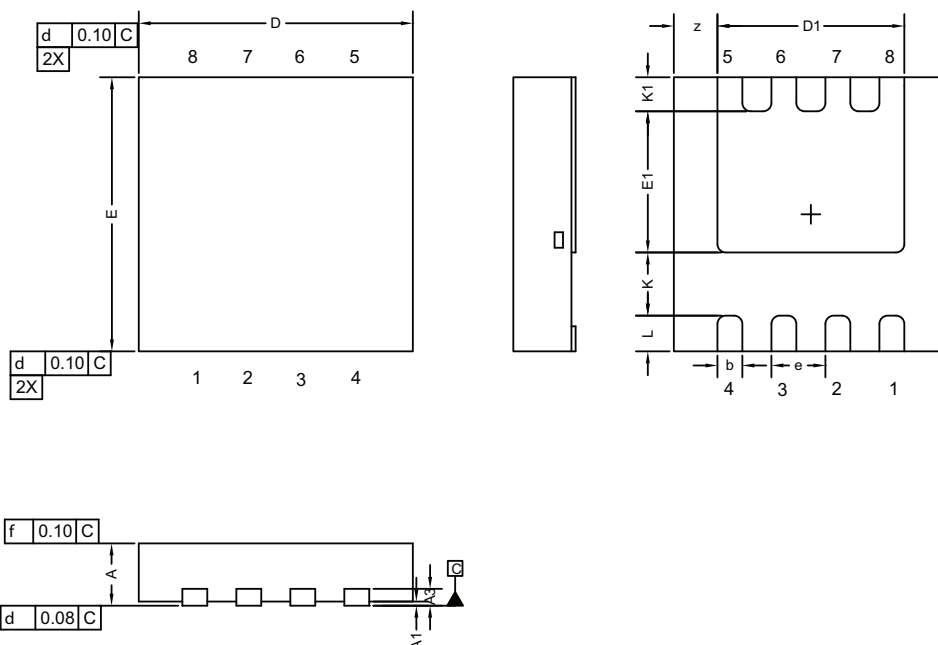


www.vishay.com

## Package Information

Vishay Siliconix

### Case Outline for PowerPAK® 1212-8S



DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.67	0.75	0.83	0.027	0.030	0.033
A1	0	-	0.05	0	-	0.002
A3	0.20 REF			0.008 REF		
b	0.30 BSC			0.012 BSC		
D	3.30 BSC			0.130 BSC		
D1	2.15	2.25	2.35	0.084	0.088	0.092
E	3.30 BSC			0.130 BSC		
E1	1.60	1.70	1.80	0.063	0.067	0.071
e	0.65 BSC			0.026 BSC		
K	0.76 TYP			0.030 TYP		
K1	0.41 TYP			0.016 TYP		
L	0.43 BSC			0.017 BSC		
z	0.525 TYP			0.021 TYP		
ECN: C12-0200-Rev. A, 12-Mar-12 DWG: 6008						

#### Note

- Millimeters will govern.

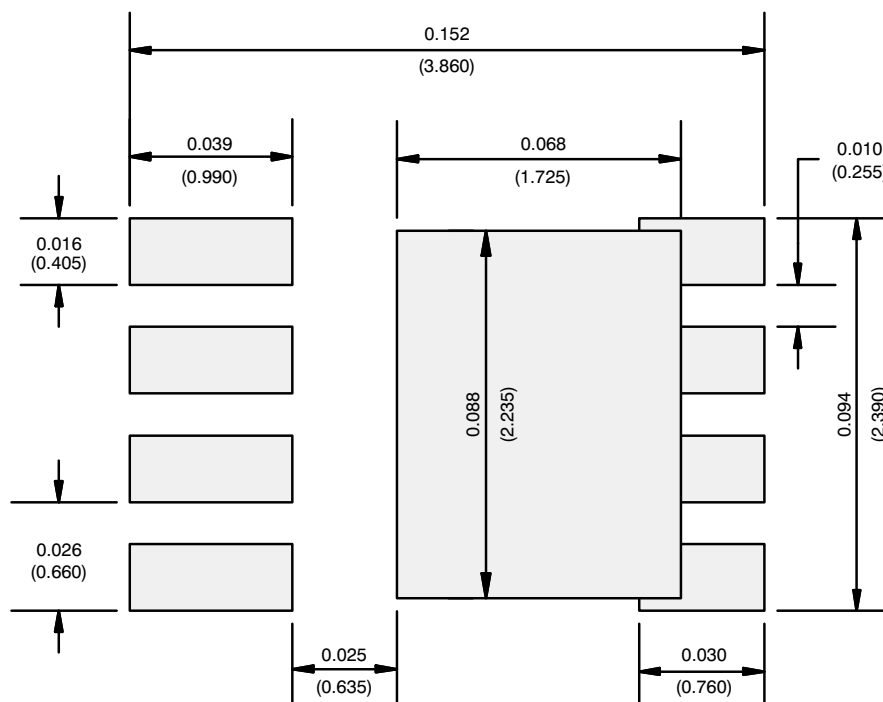




## Application Note 826

Vishay Siliconix

### RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads  
Dimensions in Inches/(mm)

[Return to Index](#)



## Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.